

# A SiGe BiCMOS 8-Channel Multi-Dithering, Sub-Microsecond Adaptive Controller

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**Abstract**—A SiGe BiCMOS mixed-signal adaptive controller-on-chip is presented that implements gradient descent of a supplied analog control objective. Eight analog variables controlling the external plant are perturbed in parallel using sinusoidal dithers, and their gradient components are estimated by parallel synchronous detection of the dithers in the control objective. Translinear all-NPN bipolar circuits achieve linear tuning of frequency and amplitude in the oscillators and synchronous detectors, covering a 4kHz-600MHz range in dither frequencies with -30dB/octave suppression of inter-modulation products. Experimental results demonstrate adaptive optimization of a 3-variable nonlinear plant within 1μs, for dithers in the 100-200MHz frequency range. The chip measures 3mm×3mm in 0.5μm SiGe and consumes 110mW at 3.3V supply.

## I. INTRODUCTION

**S**YNCHRONOUS detection is fundamental to many communications systems performing analog decoding of an amplitude-modulated carrier by measuring the component of the received signal in phase with the carrier. The same principle extends to gradient descent optimization of an objective “metric”  $J = J(u, t)$  of a plant, where the derivative  $\partial J / \partial u$ , with respect to the control variable  $u$ , is needed. This information is retrieved by superimposing a ‘dither’ signal to the control variable  $u$  and performing synchronous detection between the received perturbed objective and the dither signal.

For multiple control variables  $\mathbf{u} = (u_1, u_2, \dots, u_n)^T$  the gradient,  $\nabla J$ , of the metric  $J = J(\mathbf{u}, t)$  is estimated by applying mutually orthogonal dithers to the control variables *in parallel*, and performing synchronous detection for each of them. In the case of broad-band random dithers, this technique is known as model-free adaptation (MFA) [1] or stochastic parallel gradient descent (SPGD) [2]-[5]. Several analog hardware implementations of SPGD have been presented, most of them based on Bernoulli distributed dithers [6]-[8]. In the case of narrow-band sinusoidal dithers, the technique is known as multi-dithering (MD) [9] and has been used extensively in adaptive optics for wavefront correction.

One limitation of broad-band excitation is that delays in the plant and in evaluation of the metric distort the gradient

estimates, and thus limit the speed of gradient descent adaptation. The circuit presented here circumvents this limitation by applying narrow-band excitation using sinusoidal dithers, for which any delays in the plant and metric reduce to a single parameter, one phase for each dither. The MD circuit allows for variable phase selection in parallel synchronous detection, to compensate for arbitrary phase delay in each control channel. As with SPGD, MD gradient descent implements a model-free form of adaptive control [1], which guarantees convergence to a local optimum (minimum) of the measured control objective independent of model assumptions on the plant, and mismatch in the circuit realization of the analog controller. SiGe BiCMOS circuit implementation supports dither frequencies linearly tunable from 4kHz-600MHz, serving a wide range of applications in high-speed adaptive control for optical wavefront correction [4], [9], multi-beam optical communications [10], and aberration correction in two-photon microscopy [11], among others.

A SiGe BiCMOS current-controlled oscillator circuit that provides sinusoidal dither signals with wide tuning range is given in [12]. Architecture considerations and circuit design of the multi-dithering gradient descent adaptive control system, and first experimental results from the integrated SiGe BiCMOS implementation, are presented in [13]. Here we provide a detailed description, analysis, and experimental characterization of the circuits comprising the multi-dithering control system, quantify the system performance in terms of normalized energy efficiency, and present experimental results demonstrating closed-loop adaptation settling within 1μs at 110mW power. The multi-dithering adaptation system architecture is briefly reviewed in Section II, and circuits are described in Section III. Performance metrics are defined in Section IV, and experimentally evaluated in Section V.

## II. SYSTEM ARCHITECTURE

The presented VLSI chip contains eight identical control channels, each serving a variable of the control vector  $\mathbf{u} = (u_1, u_2, \dots, u_n)^T$  of the metric  $J(\mathbf{u}, t)$ . Two or more chips can be connected in parallel and optimize performance metrics with sixteen or more variables. Optimization of the externally presented metric  $J(\mathbf{u}, t)$  is achieved by realization of the signed version of the gradient flow algorithm and is performed in two steps: first, the gradient  $\nabla J$  is estimated through parallel synchronous detection; then, the gradient information is quantized and used to update variables  $u_i$ .

The simplified architecture of the channels is shown in Fig. 1. The sinusoidal dither of the channel is generated by one of

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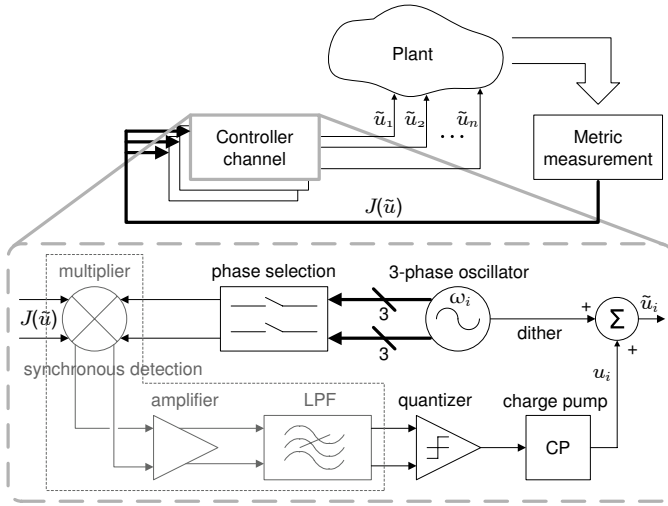


Fig. 1. System architecture of the multi-dithering adaptive optimization system, with one of the control channels shown.

the phases of a 3-phase sinusoidal oscillator, added onto the control variable  $u_i$ :

$$\tilde{u}_i = u_i + \alpha \cos(\omega_i t). \quad (1)$$

The perturbed control variables  $\tilde{\mathbf{u}} = (\tilde{u}_1, \tilde{u}_2, \dots, \tilde{u}_n)^T$  are applied to the plant under optimization, which returns a metric signal  $J = J(\tilde{\mathbf{u}})$  that is fed back to the inputs of the channels for gradient estimation. Each channel contains a linear multiplier, and an adjustable high-order low-pass filter for synchronous detection which result in a gradient estimate<sup>1</sup> [13]

$$\overline{J(\tilde{\mathbf{u}}) \cos(\omega_i t)} = \frac{\alpha}{2} \frac{\partial J}{\partial u_i} \bigg|_{\mathbf{u}}. \quad (2)$$

The multiplier output is amplified prior to low-pass filtering, since both the dither and the perturbed portion of the received metric are low in amplitude.

The total time delay  $\tau_i$  in the adaptation loop of channel  $i$  can be represented as a phase delay  $\varphi_i = \omega_i \tau_i$  which affects gradient estimation by scaling the synchronous detection output with a factor  $\cos(\varphi_i)$

$$\overline{J(\tilde{\mathbf{u}})_{\tau\text{-delay}} \cos(\omega_i t)} = \frac{\alpha}{2} \frac{\partial J}{\partial u_i} \bigg|_{\mathbf{u}} \cos(\varphi_i). \quad (3)$$

Compensation of the delay phase factor  $\cos(\varphi_i)$ , approximated with  $\pi/6$  phase quantization error, can be achieved by choosing one of three available phases of the oscillator as reference for synchronous detection, and by retaining or inverting the polarity of the gradient estimate [13]. With a phase resolution in steps of  $\pi/3$ , proper selection of one of the six phases (including polarity) leads to a residual net phase error less than  $\pi/6$ . The  $\pi/6$  phase quantization error leads to an amplitude error in the gradient estimate that is at most  $1 - \cos(\pi/6) \approx 0.134$ , producing the correct polarity of the updates and a minor reduction in the rate of convergence. A practical algorithm to dynamically select the phase  $\varphi_i$  during

<sup>1</sup>Overline denotes low-pass filtering.

closed-loop adaptation of a varying metric is given in [14]. In what follows we assume that the phase factor is maintained close to identity,  $\cos(\varphi_i) \approx 1$ .

A comparator extracts the signum of the metric's derivative  $\partial J / \partial u_i$ . The signum controls the direction of the current in the charge pump which continuously updates the value of the control variable  $u_i$  and implies (4), where  $G$  is an adjustable gain coefficient that controls the convergence rate of all channels

$$\frac{du_i}{dt} = -G \text{sgn} \left( \frac{\partial J}{\partial u_i} \bigg|_{\mathbf{u}} \right). \quad (4)$$

Equation (4) is the signed form of the gradient flow algorithm and ensures convergence of the objective metric  $J$  to a (local) extremum, as long as  $J$  has no saddle points [13]. Expansion of  $dJ/dt$  using (4) reveals the L-1 norm convergence of  $J$  with time

$$\frac{dJ}{dt} = \sum_i \frac{\partial J}{\partial u_i} \cdot \frac{du_i}{dt} = -G \left\| \frac{\partial J}{\partial \mathbf{u}} \right\|_1. \quad (5)$$

For  $G > 0$ , (5) converges to a (local) minimum of  $J$ , whereas for  $G < 0$  a (local) maximum of  $J$  is reached.

### III. CIRCUIT DESIGN AND IMPLEMENTATION

The circuit has been designed for ultra-wide frequency range tunability. To this end, a translinear architecture has been chosen and implemented in a  $0.5\mu\text{m}$  SiGe BiCMOS process providing linear tuning from 4kHz to 600MHz. An all-NPN translinear design avoids the use of inferior PNP devices in the particular SiGe process.

#### A. Oscillator

The oscillator is a differential, 3-stage,  $G_m - R - C$ , ring oscillator (Fig. 2(a)) with coupled frequency and amplitude control [12]. The Barkhausen criterion implies the following oscillation conditions

$$G_m = \frac{2}{R} \quad (6)$$

$$\text{and } \omega = \frac{\sqrt{3}G_m}{2C}. \quad (7)$$

According to (6) and (7), the frequency of oscillation can be linearly controlled through  $G_m$ , however  $R$  needs to scale inversely proportionally to  $G_m$  for oscillations to be sustained. To this end, and in order to enhance the frequency tunability range,  $G_m$  and  $R$  have been implemented as coupled translinear circuits.

Transconductance  $G_m$  is implemented by transistors  $Q_1 - Q_8$  (Fig. 2(b)) while  $R$  is the differential resistance seen between the emitters of transistors  $Q_9$  and  $Q_{10}$ . Linearizing the transconductances of the transistors in Fig. 2(b) and performing a small-signal analysis, results in  $G_m \cdot R \simeq 3$ , a gain higher than the minimum required by (6), which guarantees the existence of oscillations. Starting from a zero initial state, the amplitude of oscillation will increase until non-linearities in the circuit limit the gain  $G_m \cdot R$  to a value of 2 and the amplitude is stabilized. Assuming, for the moment,  $I_{AMP} =$

0, the values of both  $G_m$  and  $R$  are linearly proportional to  $I_{FREQ}$ , and, through (7), so is the frequency of oscillation.

Amplitude control of the oscillations is achieved by introducing current sources  $I_{AMP}$  and, thus, providing a way to adjust gain  $G_m \cdot R$ . Small-signal analysis of the translinear block in that case leads to

$$G_m \cdot R \simeq 3\alpha, \quad \alpha = \frac{I_{FREQ}}{I_{FREQ} + 2I_{AMP}}. \quad (8)$$

The Barkhausen oscillation criterion requires  $G_m \cdot R \geq 2$  (see (6)) which implies  $\frac{2}{3} \leq \alpha \leq 1$  and therefore  $0 \leq I_{AMP} \leq 0.25I_{FREQ}$ . Minimum oscillation amplitude is expected for a zero initial state with  $G_m \cdot R = 2$ , whereas maximum oscillation amplitude is achieved when the corresponding gain is  $G_m \cdot R = 3$ . The amplitude of oscillation can therefore be controlled through  $\alpha$ , or, equivalently, the ratio  $\gamma \triangleq \frac{I_{AMP}}{I_{FREQ}}$ . Oscillations of constant amplitude over a range of frequencies can be achieved by sweeping  $I_{FREQ}$  and scaling  $I_{AMP}$  proportionally, so that  $\gamma$  is kept constant.

It is worth mentioning that with the introduction of current sources  $I_{AMP}$ ,  $G_m$  no longer depends linearly on  $I_{FREQ}$ , and therefore  $I_{AMP}$  affects the oscillation frequency to second order. Detailed analysis of the amplitude dependence on  $I_{AMP}$ , and its secondary effect on oscillation frequency, is beyond the current paper and is presented in [12].

### B. Multiplier

The multiplier uses a standard Gilbert multiplier topology (Fig. 3) [15]. In order to enhance linearity, the dither input is pre-distorted. Further linearization, without compromising the translinear nature of the multiplier, is achieved by using multi-tanh “doublets”, i.e., setting a 1:4//4:1 emitter ratio for the input transistors of both the pre-distorter and the actual multiplier [16], [17].

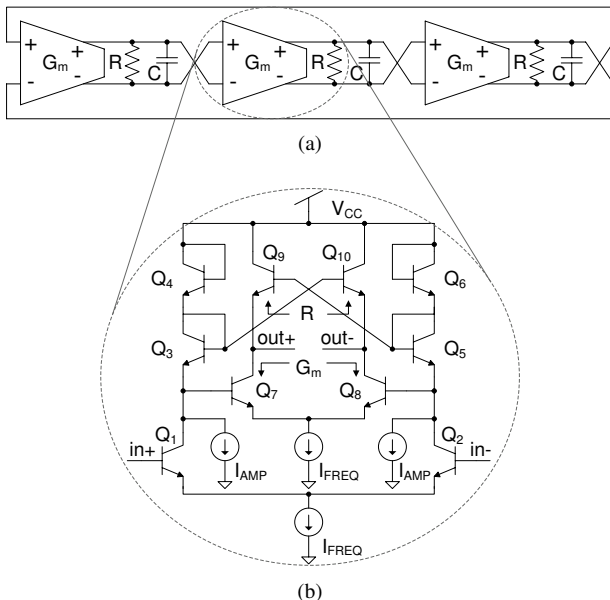


Fig. 2. (a) Architecture of the 3-phase oscillator. (b) Circuit implementation of the  $G_m - R$  blocks.

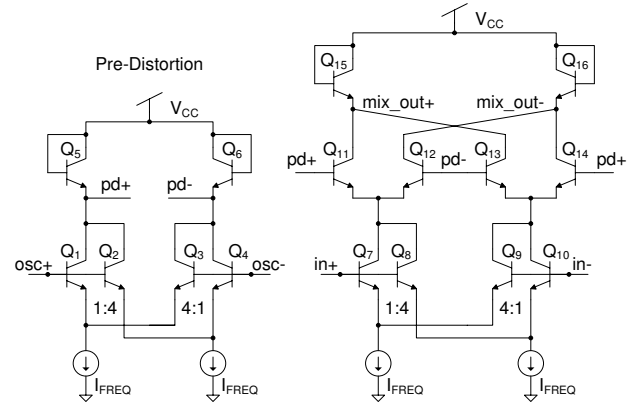


Fig. 3. The multiplier along with the pre-distortion circuit for the upper input. Ratios of 1:4 and 4:1 are used for the emitter area of the input transistors to increase linearity without compromising the translinear design.

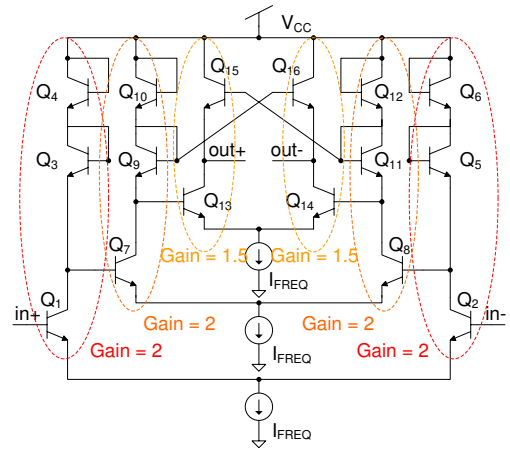


Fig. 4. Translinear amplifier with a fixed gain of 6.

### C. Amplifier

Simulation of the architecture revealed that for perturbation amplitudes  $\alpha$  below a few tens of millivolts, amplification of the product between the received metric and the dither by a factor of 6 was adequate for correct, non-saturating operation of the comparator. The amplifier is implemented as a cascade of three differential translinear gain stages, biased with the same current as that of the oscillator, as shown in Fig. 4.

### D. Low-Pass Filter

Two competing requirements set a trade-off in selecting the cut-off frequency of the low-pass filter: on one hand the cut-off frequency is directly related to the system's closed-loop bandwidth and therefore needs to be set high for fast adaptation speeds; on the other hand, a lower cut-off frequency allows for closer spacing between dither frequency bands and thus an increased number of control channels within a specific bandwidth. The trade-off can be loosened using a high order low-pass filter.

In the proposed architecture a 5<sup>th</sup> order Chebyshev topology with 1dB ripple is implemented, offering a 30dB/octave attenuation beyond the cut-off frequency. The low-pass filter





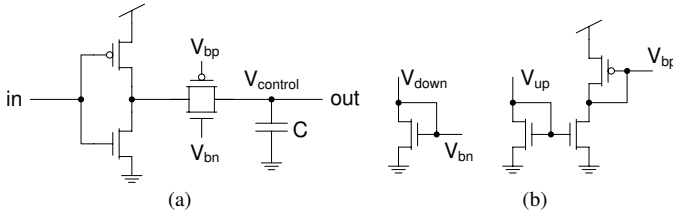


Fig. 7. (a) Charge pump with individual biases for the up and down rates. (b) Biasing circuits.

orthogonal, so that the gradient estimates are unbiased<sup>2</sup>.

### B. Linearity of the Oscillator

To assess the effect of dither harmonics on the accuracy of gradient estimation, consider the system architecture in Fig. 1. If the dither signals are pure sinusoids of frequencies  $\omega_i$ ,  $i = 1, \dots, n$  and of relatively small amplitudes, then, the interference between the channels is limited as long as  $|\omega_i - \omega_j|$ ,  $\forall i \neq j$  exceed the cut-off frequencies of the corresponding filters. In this case the inter-channel interference is only due to the nonlinearities of the cost metric  $J$  and the multipliers.

In practice, harmonic components always exist and careful assignment of the dither frequencies is needed. The higher the linearity of the oscillator, the more arbitrarily these frequencies can be chosen. On the other hand, by appropriate selection of the  $\omega_i$ 's, such that no intermodulation product falls within the bandwidth of the filter, any effect of harmonics in the multi-variable detection scheme could be avoided. In principle, even square dithers can be used as long as due care is taken in the selection of the dither frequencies, although the dither frequency constraints do not facilitate a large number of

<sup>2</sup>In the limit of very large phase noise, the dithers become broadband noise signals, and the multi-dithering optimization reduces to stochastic parallel gradient descent [2]-[5]. Practical levels of phase noise retain the narrow-band frequency property of the dither signals, necessary for delay-insensitive model-free adaptation [24], [14].

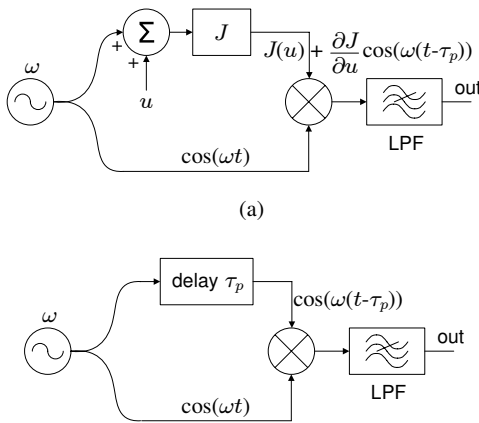


Fig. 8. (a) Simplified model of the synchronous detection scheme for closed-loop operation of the proposed architecture. (b) Simplified model of the delay line discriminator.

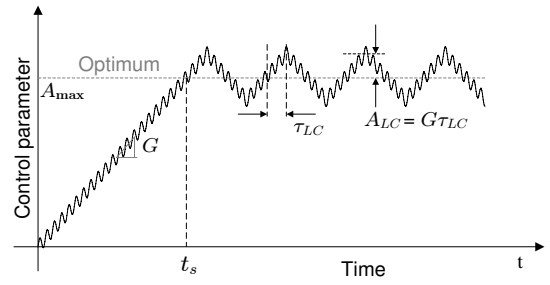


Fig. 9. Limit cycle fluctuations at steady state, for single parameter adaptation with constant-modulus updates.

control channels and impose severe bandwidth constraints on the available adaptation bandwidth.

### C. Convergence

The hard-limiting nature of the comparator in the loop implies a steady state, possibly aperiodic, oscillatory pattern in the control parameters  $u_i$  after convergence. In the case of a single control parameter, the steady state oscillations are periodic and take the form of a limit cycle of alternating increments and decrements in  $u$ , at a frequency determined by the group delay of the adaptation loop  $\tau_{LC}$ , as shown in Fig. 9. The triangular pattern of the limit cycle in the control variable  $u$  induces a near-sinusoidal pattern after synchronous detection, at the output of the low-pass filter. In turn, the square form of the quantized output generates charge pump updates that sustain, after integration onto the capacitor, the triangular pattern of fluctuations  $u$  around the optimum value of the control parameter. Note that the frequency of the limit cycle,  $1/(4\tau_{LC})$ , is at most equal to the cut-off frequency of the low-pass filter (and therefore much lower than that of the sinusoidal dithers  $\delta u_i = \cos(\omega_i t)$ ), since, otherwise, limit cycles would not be sustained.

The frequency of the limit cycle is directly related to the group delay of the adaptation loop and therefore to parameters such as the delay introduced by the unknown plant, the metric estimation and feedback propagation as well as circuit blocks of the controller, such as the low-pass filter. On the other hand, the amplitude  $A_{LC}$  of the limit cycle depends both on the frequency of the limit cycle as well as the gain  $G$  in the update rule of the gradient descent algorithm. Finally, the settling time  $t_s$  for the convergence of a control parameter to its optimum value is proportional to  $G$ . For a given group delay (directly related to  $\tau_{LC}$ ), the trade-off between settling time and amplitude of the limit cycle is apparent; higher gain  $G$  leads to faster convergence but also higher fluctuation around the optimum value and vice versa.

For the general case of  $n$  control parameters, the general observation, that amplitude  $A_{LC}$  and gain  $G$  are directly related through the delay  $\tau_{LC}$ , is still valid. The behavior of the parameters at steady state can be described as coupled bounded-amplitude oscillations around the optimal values. Analysis of the dynamics of the steady state oscillatory pattern in the multi-dimensional case is beyond the current paper.

#### D. Power Efficiency

The translinear BJT circuit design throughout major parts of the architecture offers, besides wideband operation with current bias control over several decades in frequency, also bias-invariant power efficiency, in that power consumption scales with the adaptation speed. Power calculation can be performed by taking into account the  $G_m - C$  nature of the circuits and noting that the bandwidth of each stage is proportional to

$$f_{BW} = \frac{G_m}{C_{eff}} \propto \frac{I_{bias}}{C_{eff}}, \quad (9)$$

where  $C_{eff}$  is the overall capacitance at the output node of the stage. According to (9), power consumption for each stage, which is proportional to the bias current  $P \propto I_{bias} \cdot V_{supply}$ , scales directly with the bandwidth  $f_{BW}$  of each stage.

In a typical scenario of selecting the bandwidth and therefore the bias currents for each stage of the system, one starts by determining the bandwidth of the cost function  $J$ ,  $f_{-3dB,J}$ . Accordingly the (radial) dither frequencies  $\omega_i$  (where  $\omega_i = 2\pi f_i$ ) for each channel are set below  $2\pi f_{-3dB,J}$ . The optimal choice of the dither frequencies is a uniform distribution between a user-selectable lowest frequency  $\omega_1$  and  $\omega_n \lesssim 2\pi f_{-3dB,J}$ . Added convenience is provided by setting  $\Delta\omega/\omega_{av} = 1/k = \text{constant}$ , where  $\Delta\omega = |\omega_i - \omega_j|$ ,  $\forall i \neq j = 1, \dots, n$  and  $\omega_{av} = \frac{1}{n} \sum_{i=1}^n \omega_i$ , so that the selection of the dither frequencies scales in a standard way, for any  $f_{-3dB,J}$ . Under these conditions, the mean power dissipated from the oscillator stage can be written as (see also Section III-A)

$$P_{osc,av} = m_{osc} \cdot I_{FREQ,av} \cdot V_{supply} \propto \omega_{av} \cdot V_{supply}. \quad (10)$$

where  $m_{osc}$  is a factor representing the multiplicity of current  $I_{FREQ,av}$  in the oscillator stage. More specifically, assuming that  $I_{AMP}$  scales proportionally to  $I_{FREQ}$  with a factor  $\gamma$  for all channels, and referring to Figs. 2(a) and (b), we conclude that  $m_{osc} = 6(1 + \gamma)$ .

The bias current of both the multiplier and the amplifier, for each channel  $i$ , is set equal to  $I_{FREQ,i}$ , so that, according to (9), their bandwidth scales proportionally to frequency  $\omega_i$ . Therefore, the average power consumed at these stages also scales according to  $\omega_{av}$  and can be written as

$$P_{mix-amp,av} = (m_{mix} + m_{amp}) \cdot I_{FREQ,av} \cdot V_{supply}. \quad (11)$$

where  $m_{mix} = 4$  for the design of the multiplier in Fig. 3, and  $m_{amp} = 3$  for the design of the amplifier in Fig. 4.

The cut-off frequency of the low-pass filter needs to be set lower than  $\Delta\omega/2$ , so that all intermodulation products are attenuated by at least 30dB. Since the bandwidth of the filter for each channel is set through bias current  $I_{LPF}$  (see Section III-B), the power  $P_{LPF}$  consumed at this stage is  $P_{LPF} = m_{LPF} \cdot I_{LPF} \cdot V_{supply}$  and scales according to  $\Delta\omega$ . Assuming  $\omega_{av} = k \cdot \Delta\omega$ ,  $P_{LPF}$  can be rewritten as

$$P_{LPF} = \frac{m_{LPF}}{\eta \cdot k} \cdot I_{FREQ,av} \cdot V_{supply}, \quad (12)$$

where  $I_{FREQ,av} = k \cdot I_{LPF}$  can be assumed because of the linear relationship between  $\Delta\omega$ ,  $\omega_{av}$  and  $I_{LPF}$ ,  $I_{FREQ,av}$ ,

respectively. Parameter  $\eta \geq 2$  represents the ratio between  $\Delta\omega$  and the (radial) cut-off frequency of the filter.

Strictly speaking, the linear relation between power, bandwidth and oscillator bias current is not valid for the entire multi-dithering control architecture, since some of the building blocks in particular the comparators and the output buffers are implemented using MOSFETS biased in the above threshold regime, where the MOSFET transconductance exhibits a square-root dependence on bias current. Nonetheless, overall the bandwidth scales approximately linearly with the oscillator bias and thus adaptation speed scales roughly linearly in power.

#### E. Figure of Merit

In order to compare the performance of the presented architecture with adaptive systems previously presented in literature, the following figure of merit (FOM) is here proposed

$$\text{FOM} = \frac{BW \cdot SNR \cdot n}{P} \quad (13)$$

where  $BW$  is the adaptation bandwidth equivalent to the inverse of settling time  $t_s$  (Fig. 9),  $SNR = A_{\max}/A_{LC}$  is the signal-to-noise ratio between the desired transition voltage  $A_{\max}$  and the amplitude  $A_{LC}$  of the steady state (limit-cycle or aperiodic) oscillations due to the signed constant-modulus updates (Fig. 9),  $n$  is the number of channels for which adaptation is demonstrated, and  $P$  is the total dissipated power.

From the above definition of bandwidth and referring to Fig. 9, parameter  $BW$  can be rewritten as  $BW = G/A_{\max}$ , in which case the product  $BW \cdot SNR$  collapses to

$$BW \cdot SNR = \frac{G}{A_{\max}} \cdot \frac{A_{\max}}{A_{LC}} = \frac{1}{\tau_{LC}}.$$

For comparison purposes, it is worthwhile to contrast the constant-modulus updates (4) to adaptive circuits and systems that implement a linear unthresholded form of gradient updates. For the case of linear updates, where convergence is inverse exponential and no oscillatory behavior is observed, the FOM definition of (13) can be directly evaluated by expressing  $SNR$  explicitly, and by expressing  $BW$  as the inverse of the settling time. Thus, at  $SNR = 1$ , the FOM for systems with linear and constant-modulus updates can be directly compared, by comparing the settling time  $t_s$  of the linear system with the delay  $\tau_{LC}$  for the constant-modulus system (or a quarter of the period of the limit-cycles, see Fig. 9). For higher values of  $SNR$ , values of  $t_s$  should be accordingly scaled in the comparison with  $\tau_{LC}$ .

#### V. EXPERIMENTAL MEASUREMENTS

The 8-channel multi-dithering controller was implemented on a 3mm×3mm chip fabricated in 0.5μm SiGe BiCMOS technology. A micrograph of the chip and a detailed view of one of the eight channels are shown in Figs. 10(a) and (b) respectively.

Figure 11(a) shows the linear operating frequency range of the oscillator, extending to more than 5 decades (from below 4kHz to above 600MHz) and the linear dependency of the frequency on the biasing current  $I_{FREQ}$ . The frequency and

amplitude of the signal were measured for 3 different values of ratio  $\gamma$ . As can be seen in Fig. 11(a), for a given value of  $I_{FREQ}$ , the amplitude of oscillation can be controlled by the value of  $\gamma$ . For  $\gamma = 0$ , a maximum differential amplitude of  $60\text{mV}_{pp}$  (corresponding to a single-ended measurement of  $30\text{mV}_{pp}$  or  $\sim 30\text{dBm}$  on a  $50\Omega$  load) is reached, for most of the frequency range. The dependency of the oscillation frequency with  $\gamma$  (and therefore  $I_{AMP}$ ), discussed in Section III-A, can be also observed.

Figure 11(b) shows the spectral content of the oscillator output signal for  $I_{FREQ} \simeq 40\mu\text{A}$  and  $\gamma = 0$ . The oscillator signal is observed at the control output  $u_i$  for one of the channels. This output conveys an AC coupled single-ended version of the internally differential oscillator signal. The effect of harmonic distortion on adaptation performance is negligible as long as dithers of different channels are not harmonically related (Section IV-B). Since synchronous detection makes use of differential signals (for one of the oscillator phases), only the odd-order harmonics are relevant to assess linearity in synchronous detection. For other applications of the very wide frequency range tunable oscillator where harmonic distortion may be an issue, differential measurements directly from an isolated oscillator circuit are included in [12].

The transfer function of the low-pass filter was measured for 4 different values of  $I_{LPF}$  and the results are shown in Fig. 12. For biases of  $66.2\text{nA}$ ,  $814\text{nA}$ ,  $10.6\mu\text{A}$  and  $128\mu\text{A}$ , the measured cut-off frequencies correspond to  $200\text{kHz}$ ,  $2\text{MHz}$ ,  $20\text{MHz}$  and  $200\text{MHz}$ , respectively, spanning a tuning range of at least 4 decades. Measurements of the filter transfer function for lower values of  $I_{LPF}$  were limited by the operating range of our measuring equipment. Moreover, the seemingly lower stop-band rejection at higher cut-off frequencies is due to higher resolution and video bandwidths in the spectrum analyzer used to acquire the data, which, in turn, increased the noise floor in the measurements. Note, finally, the linear relation between the control bias and the corresponding bandwidth of the filter.

To demonstrate synchronous detection performance, four channels were perturbed with oscillation frequencies of  $97\text{MHz}$ ,  $122\text{MHz}$ ,  $139\text{MHz}$  and  $160\text{MHz}$ . Their outputs were

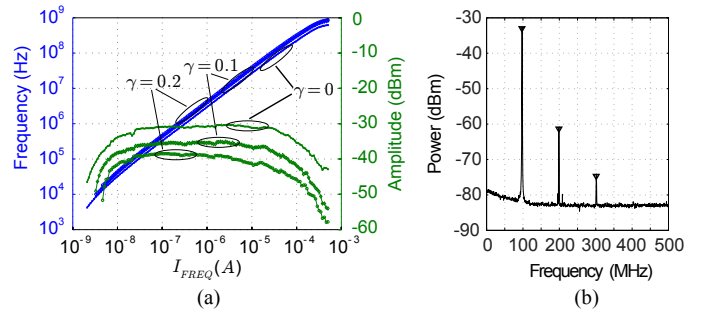


Fig. 11. (a) Oscillation frequency and amplitude with respect to current  $I_{FREQ}$  recorded for 3 different values of  $\gamma$ . Operating frequencies range below  $4\text{kHz}$  and above  $600\text{MHz}$ . (b) Spectrum of oscillator's output measured for  $I_{FREQ} \simeq 40\mu\text{A}$  and  $\gamma = 0$ . The amplitude of oscillation from the single-ended output is  $\simeq 20\text{mV}_{pp}$ .

summed, using an RF power combiner, resulting in a multi-tone signal whose spectrum is shown in Fig. 13(a). The combined signal was fed back, single-ended, to the metric input of the chip. Figure 13(b) shows the spectrum after multiplication with the  $139\text{MHz}$  signal, but before any filtering. The expected products around  $20\text{MHz}$  and  $40\text{MHz}$  are present. Fig. 13(c) displays the spectrum at the output of the low-pass filter following the multiplier. The cut-off frequency has been set to approximately  $10\text{MHz}$ . Components above that frequency are significantly attenuated down to the noise floor. Comparison of Figs. 13(b) and (c) shows also the expected  $30\text{dB/octave}$  attenuation of the signal at  $20\text{MHz}$  due to the  $5^{\text{th}}$  order filter. Note also the sharp peak of the fundamental synchronous detection component at DC frequency, in contrast to the significantly wider spurs. This is consistent with the observation on the immunity of synchronous detection to phase noise as noted in Section IV.

The influence of metric delay in gradient estimation has been studied and the effect of phase selection on the phase error of the estimate has been validated based on the following experiment. The loop was closed by connecting the output of a single channel to the metric input using a transmission line of considerable time delay  $\tau$ . In this case, the metric is  $f(x(t)) = x(t - \tau)$  and the adaptation rule dictates a continuous increase

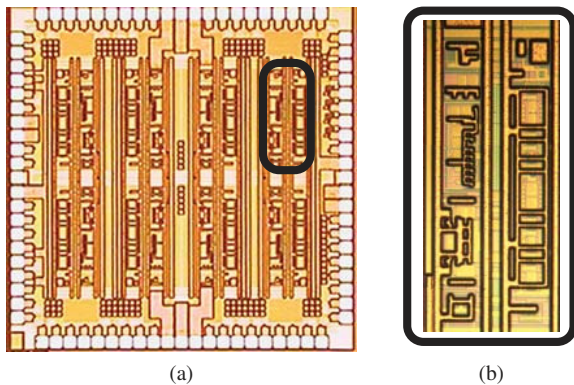


Fig. 10. (a) Chip microphotograph and (b) single channel detail. Dimensions of the chip are  $3\text{mm} \times 3\text{mm}$ , and the cell measures  $500\mu\text{m} \times 900\mu\text{m}$ , in  $0.5\mu\text{m}$  SiGe BiCMOS technology.

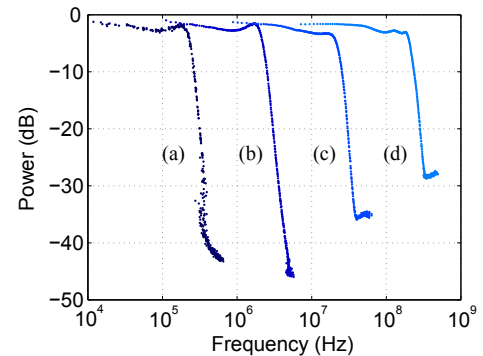


Fig. 12. Transfer function of the filter measured for 4 different values of bias  $I_{LPF}$  (a)  $66.2\text{nA}$ , (b)  $814\text{nA}$ , (c)  $10.6\mu\text{A}$  and (d)  $128\mu\text{A}$ . The achieved cut-off frequencies are  $200\text{kHz}$ ,  $2\text{MHz}$ ,  $20\text{MHz}$  and  $200\text{MHz}$  respectively.



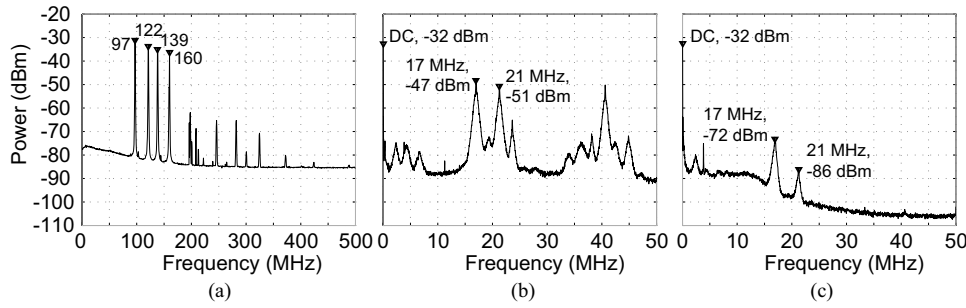


Fig. 13. (a) Spectrum of the combination of four channel outputs with channel dither frequencies at 97MHz, 122MHz, 139MHz and 160MHz. The combined signal is fed to the input of the chip. (b) Recorded spectrum after multiplying the multi-tone signal with the 139MHz dither. (c) Recorded spectrum after low-pass filtering of the multipliers' output (cut-off at 10MHz).

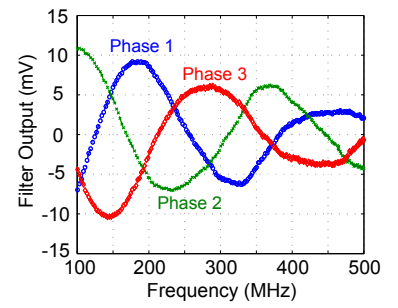


Fig. 14. Synchronous detection output measured for a metric containing a single delayed dither, for different phase selections.

in the control voltage of the channel, until saturation. Fig. 14 shows the change in filter output voltage versus dither frequency due to variable phase delay, introduced by the delay line, for each of the 3 oscillator phases selected as inputs to the synchronous detection. The three curves consistently show the  $120^\circ$  separation in phase according to the 3 oscillator phases. For any given phase selection, the delay of the line causes the sign of the output to change with frequency. However, for any given frequency, at least one of the 3 phases produces the correct sign of the derivative estimate. Correct phase selection is critical for convergence at high dither-frequency  $\times$  time-delay products [24], and an algorithm for adaptively selecting the optimal phase is given in [14].

The relation between the control biases  $V_{bp}$  and  $V_{bn}$  of the charge pump and the corresponding update rates was characterized by the measurements shown in Fig. 15. The up-rate corresponds to how fast the capacitor of the charge pump is charged through the PMOS current source, and is controlled by  $V_{bp}$ . The down-rate corresponds to the discharge of the capacitor through the current sink of the NMOS, and is controlled by  $V_{bn}$ . Through appropriate biasing, the update rates can take values from below  $1\text{V}/\mu\text{s}$  to above  $10^6\text{V}/\mu\text{s}$ .

The closed-loop performance of the system was evaluated using an external circuit that serves as an analog plant with a characteristically nonlinear min-max cost metric. The simplified schematic of the external plant, implemented with resistors

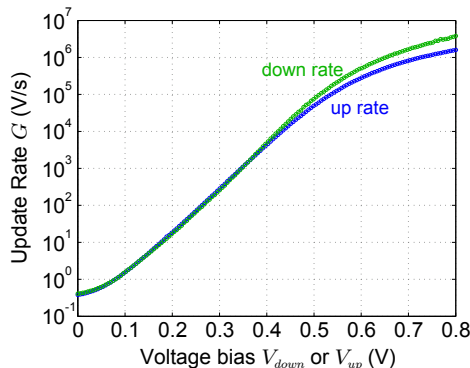


Fig. 15. Update rates  $G$  by the charge pump, measured as a function of voltage bias  $V_{down}$  and  $V_{up}$ .

and diodes, is shown in Fig. 16. The differential output  $V_{max} - V_{min}$  realizes approximately the metric  $f(V_1, \dots, V_n, V_{ref}) = \max(V_1, \dots, V_n, V_{ref}) - \min(V_1, \dots, V_n, V_{ref}) - 2V_F$ , where  $V_i > 0$ ,  $i = 1, \dots, n$  are the voltage outputs from  $n$  channels of the system,  $V_{ref} > 0$  is a reference voltage provided by a function generator, and  $V_F$  is the forward voltage drop of the used diodes. The metric  $f$  has a global minimum equal to  $-2V_F$ , reached when  $V_1 = V_2 = \dots = V_n = V_{ref}$ . Fig. 17 shows how the outputs from 3 channels ( $V_1$ ,  $V_2$  and  $V_3$ ) adapt to a  $100\text{kHz}$  triangular reference voltage  $V_{ref}$  of  $500\text{mV}_{p-p}$  amplitude, minimizing the output of the metric. The dithers of the 3 channels were set at  $90\text{MHz}$ ,  $120\text{MHz}$  and  $150\text{MHz}$ .

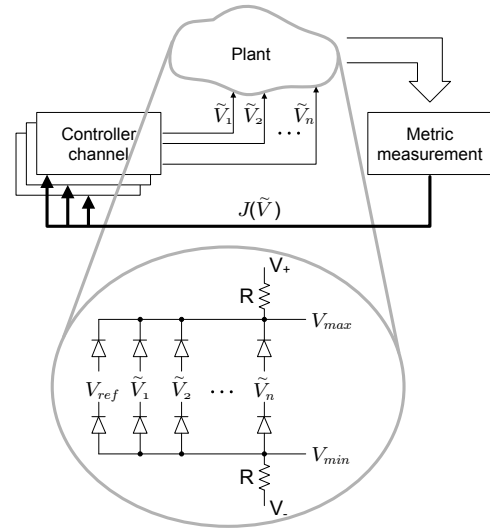


Fig. 16. Experimental setup for characterization of closed-loop controller dynamics. A metric function  $f(V_1, \dots, V_n, V_{ref}) = \max(V_1, \dots, V_n, V_{ref}) - \min(V_1, \dots, V_n, V_{ref}) - 2V_F$  is provided by an external analog plant, implemented using diodes and resistors.

To test the adaptation speed of the system, the same diode-based external circuit supplying the min-max metric was used, but the reference was set to a  $500\text{mV}_{p-p}$  square wave. The gain of the charge pump was adjusted so as to achieve fast adaptation with tolerable limit cycles. Fig. 18 shows results for the case of a single channel control voltage perturbed at  $90\text{MHz}$ . At each transition of the square wave, tracking



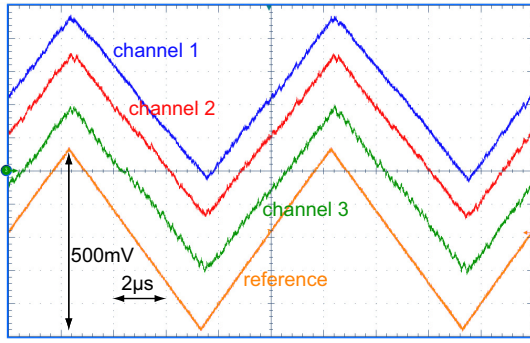


Fig. 17. Experimental adaptation of 3 channels to a 100kHz triangular reference waveform. Exact tracking of the reference indicates minimization of the metric function. Dithers are set at 90MHz, 120MHz and 150MHz.

is momentarily lost (peaks in the metric) before the channel output signal reaches the new level of the reference voltage. The minimum value of the metric is  $-650\text{mV}$ , and very close to  $-2V_F$  ( $\approx -700\text{mV}$ ). Adaptation is achieved in less than  $1\mu\text{s}$ .

The experimental results of closed-loop adaptation shown here are typical, and are consistent across several channels across several chips. Because of differences in dither frequencies and corresponding phase differences in the control loop, it was necessary to individually adjust the phase parameters for each channel. A practical procedure for selecting the phase parameters is given and demonstrated in [14]. No other parameters required tuning, although we observed that for certain control metrics it was necessary to amplify the external metric signal, so that the gains  $\partial J/\partial u_i$  exceed a given threshold, in order for all channels to lock into closed-loop adaptation. We

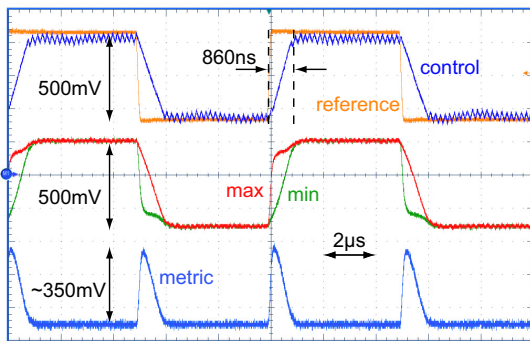


Fig. 18. Single channel control tracking a 100kHz square waveform. With dither set at 90MHz, adaptation is achieved in less than  $1\mu\text{s}$ .

TABLE I  
CHIP DESIGN PARAMETERS AND MEASURED PERFORMANCE

Process	SiGe BiCMOS $0.5\mu\text{m}$
Area	$3\text{mm} \times 3\text{mm}$
Channels	8
Linear Dither Frequency Range	4kHz - 600MHz
Update Rate	$0.4 - 4 \cdot 10^6 \text{ V/s}$
Adaptation Speed	$< 1\mu\text{s}$
Power for dithers at 12MHz-20MHz	50mW
Power for dithers at 120MHz-200MHz	110mW

traced this sensitivity in the amplitude of the control metric to analog mismatch in the circuit realization of the comparator in the synchronous detector (Fig. 6). An offset-independent, auto-adaptive comparator that alleviates this sensitivity is described in [32], whereas an alternative approach could be a wideband comparator with adaptable offset as presented in [33].

Measured power dissipation for simultaneous operation of all 8 channels ranges between 50mW for dither frequencies in the range of 12-20MHz and 110mW for dither frequencies of 120-200MHz. The design parameters and measured performance of the chip is summarized in Table I.

Finally a comparison between the proposed architecture and other adaptive controller implementations reported in literature was performed. The comparison included recently presented adaptive systems, both analog and digital, for which chip data were provided, without any constraints on the application for which they were used for. Lack of the  $SNR$  information for most references prohibited full evaluation of the proposed FOM in Section IV-E and therefore comparison was limited to the 3 other design variables comprising the FOM: the number of controlled parameters  $n$ , the power consumed by the controller  $P$ , and the lowest reported adaptation time  $t_s$ . The collected data is shown in Table II. A visual representation of Table II data is shown in Fig. 19 where the horizontal axis represents power per control channel  $P/n$  and the vertical axis the minimum reported adaptation time  $t_s$ . On the logarithmic display, lines in the graph indicate equal values of FOM, for a given  $SNR$ .

## VI. CONCLUSION

A VLSI implementation of a model-free architecture for adaptive control, using narrow-band multi-dithering gradient descent, has been presented. A fully translinear implementation using a SiGe BiCMOS process provides linear tunability

TABLE II  
COMPARISON BETWEEN HIGH-SPEED VLSI ADAPTIVE CONTROLLERS

Reference	[25]	[26]	[27]	[28]	[29]	[30]	[31]	This work
Process	$2\mu\text{m}$ CMOS	$0.4\mu\text{m}$ CMOS	$0.13\mu\text{m}$ CMOS	$0.13\mu\text{m}$ CMOS	$0.25\mu\text{m}$ CMOS	$0.25\mu\text{m}$ CMOS	IBM SiGe	$0.5\mu\text{m}$ SiGe BiCMOS
Parameters	4	4	4	4	2	1	4	8
Power (mW)	236	43	100	N/A	43.2	5.7	N/A	110
Adaptation time ( $\mu\text{s}$ )	20	10	25	20	25	80	100	1

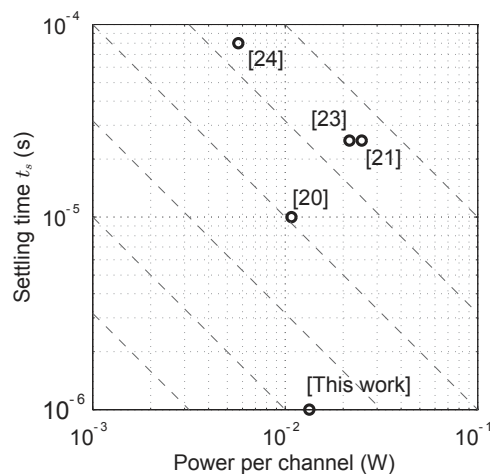


Fig. 19. Comparison of the presented work with previous reported adaptive controller implementations, in terms of settling time and consumed power per channel. Lines shown in the graph indicate equal values of FOM, for a given SNR.

over 5 decades of frequency. Characterization and closed loop experiments demonstrate synchronous detection and metric adaptation up to 200MHz dither frequencies, at 110mW power consumption.

## VII. ACKNOWLEDGMENTS

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